

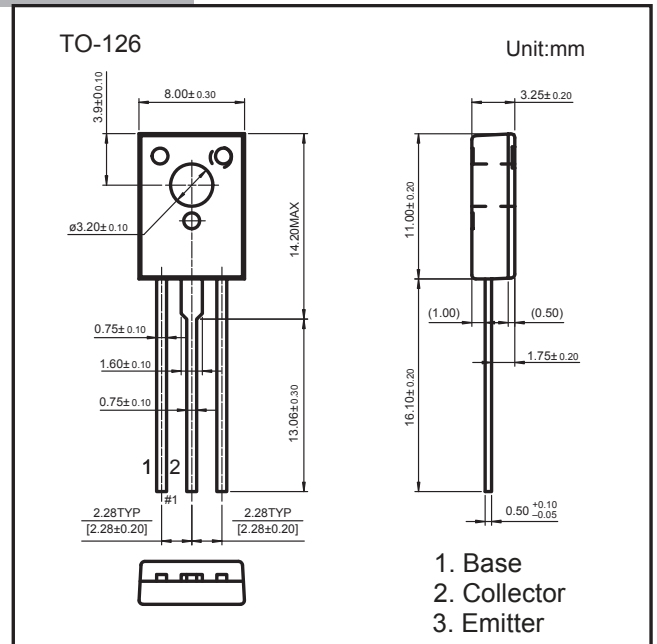
TO-126 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Power Amplifier
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-126 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Emitter Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2.5	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC1162	TO-126	Bulk	200pcs/Bag
2SC1162-TU	TO-126	Tube	60pcs/Tube

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1mA, I_E = 0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1mA, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 35V, I_E = 0$			20	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			20	μA
DC current gain	h_{FE1}	$V_{CE} = 2V, I_C = 0.5A$	60		320	
	h_{FE2}	$V_{CE} = 2V, I_C = 1.5A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 200mA$			1	V
Base-collector voltage	V_{BE}	$V_{CE} = 2V, I_C = 1.5A$			1.5	V
Transition frequency	f_T	$V_{CE} = 2V, I_C = 200mA$		180		MHz

-pulse test

CLASSIFICATION OF h_{FE1}

Rank	B	C	D
Range	60-120	100-200	160-320

Type	2SC1162
Marking	C1162